

Title (en)

THERMOELECTRIC CONVERSION MATERIAL AND METHOD FOR MANUFACTURING SAME

Title (de)

THERMOELEKTRISCHES UMWANDLUNGSMATERIAL UND VERFAHREN ZUR HERSTELLUNG DAVON

Title (fr)

MATÉRIAU DE CONVERSION THERMOÉLECTRIQUE ET SON PROCÉDÉ DE FABRICATION

Publication

**EP 2843720 B1 20171018 (EN)**

Application

**EP 13782240 A 20130417**

Priority

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Abstract (en)

[origin: EP2843720A1] The present invention provides a thermoelectric conversion material having a reduced thermal conductivity and having an improved figure of merit, and a method for producing the material. The thermoelectric conversion material has, as formed on a resin substrate having recesses, a thermoelectric semiconductor layer formed of a thermoelectric semiconductor material, wherein the resin substrate comprises one formed by curing a resin layer of a curable resin composition. The production method for the thermoelectric conversion material comprises a resin substrate formation step of transcribing a protruding structure from an original plate having the protruding structure onto a resin layer of a curable resin composition and curing the layer, and a film formation step of forming a thermoelectric semiconductor layer of a thermoelectric semiconductor material on the resin substrate.

IPC 8 full level

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